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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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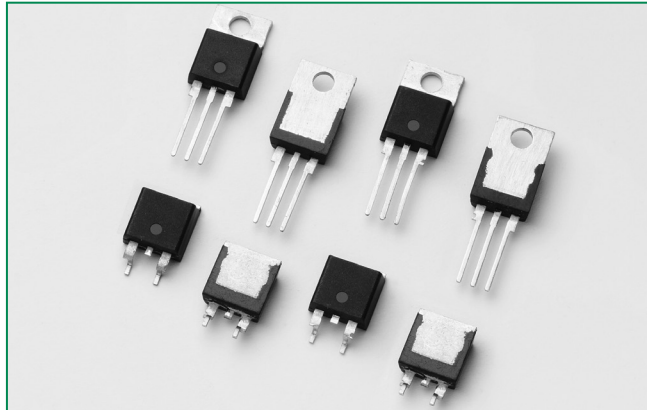
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**SJxx40x Series**



**Description**

This SJxx40x high temperature SCR series is ideal for uni-directional switch applications such as phase control in heating, motor speed controls and AC rectifier and voltage regulator.

These SCRs have a low gate current trigger level of 40 mA maximum at approximately 1.5 V, with a sensitive version of this series having a gate trigger current of 15 mA maximum.

**Features & Benefits**

- High junction temperature
- Voltage capability up to 600 V
- Surge capability up to 520 A at 60 Hz half cycle
- Halogen free and RoHS compliant

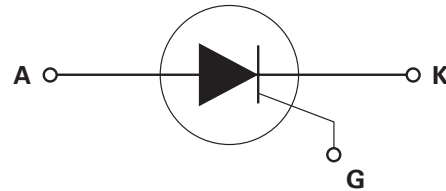
**Applications**

Typical applications are AC rectifier, voltage regulator, AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

**Main Features**

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
$V_{DRM}/V_{RRM}$	400 or 600	V
$I_{GT}$	40	mA

**Schematic Symbol**



**Absolute Maximum Ratings**

Symbol	Parameter	Test Conditions	Value	Unit
$V_{DSM}/V_{RSM}$	Peak non-repetitive blocking voltage	$P_w = 100\mu s$	700	V
$I_{T(RMS)}$	RMS on-state current	$T_c = 120^\circ C$	40	A
$I_{T(AV)}$	Average on-state current	$T_c = 120^\circ C$	25.0	A
$I_{TSM}$	Peak non-repetitive surge current	single half cycle; $f = 50Hz$ ; $T_J$ (initial) = $25^\circ C$	430	A
		single half cycle; $f = 60Hz$ ; $T_J$ (initial) = $25^\circ C$	520	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3 ms$	1122	$A^2s$
$di/dt$	Critical rate of rise of on-state current	$f = 60Hz$ ; $T_J = 150^\circ C$	150	$A/\mu s$
$I_{GM}$	Peak gate current	$t_p \leq 10\mu s$ ; $T_J = 150^\circ C$	4	A
$P_{G(AV)}$	Average gate power dissipation	$t_p \leq 10\mu s$ ; $T_J = 150^\circ C$	1	W
$T_{stg}$	Storage temperature range		-40 to 150	$^\circ C$
$T_J$	Operating junction temperature range		-40 to 150	$^\circ C$

**Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified)**

Symbol	Test Conditions		SJxx40x	SJxx40x2	Unit	
I <sub>GT</sub>	V <sub>D</sub> = 12V; R <sub>L</sub> = 30 Ω	MAX.	40	15	mA	
		MIN.	5	3		
V <sub>GT</sub>		MAX.	1.5		V	
dv/dt	V <sub>D</sub> = V <sub>DRM</sub> ; gate open; T <sub>J</sub> = 125°C	400V	MIN.	650	400	V/μs
		600V		600	350	
	V <sub>D</sub> = V <sub>DRM</sub> ; gate open; T <sub>J</sub> = 150°C	400V		550	300	
		600V		500	250	
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> ; R <sub>L</sub> = 3.3 kΩ; T <sub>J</sub> = 150°C	MIN.	0.2		V	
I <sub>H</sub>	I <sub>T</sub> = 400mA (initial)	MAX.	60	50	mA	
t <sub>q</sub>	I <sub>T</sub> =2A; t <sub>p</sub> =50μs; dv/dt=5V/μs; di/dt=-30A/μs	MAX.	35		μs	
t <sub>gt</sub>	I <sub>G</sub> = 2 x I <sub>GT</sub> ; PW = 15μs; I <sub>T</sub> = 80A	TYP.	2		μs	

NOTE: xx = voltage, x = package

**Static Characteristics**

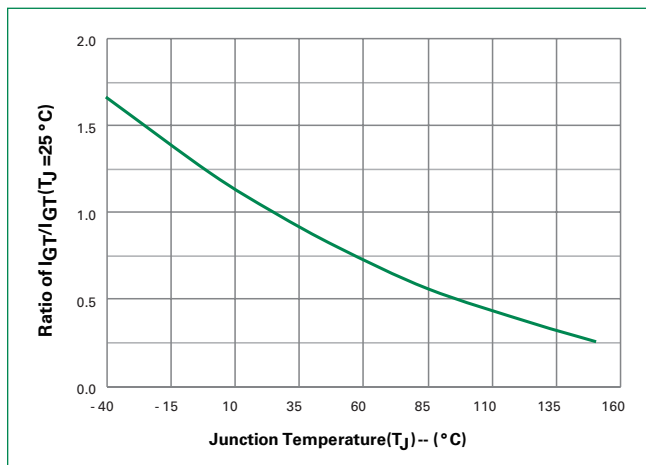
Symbol	Test Conditions		Value	Unit	
V <sub>TM</sub>	I <sub>T</sub> = 80A; t <sub>p</sub> = 380μs		MAX.	1.7	V
I <sub>DRM</sub> / I <sub>RRM</sub>	@ V <sub>DRM</sub> / V <sub>RRM</sub>	T <sub>J</sub> = 25°C	MAX.	10	μA
		T <sub>J</sub> = 125°C		2000	
		T <sub>J</sub> = 150°C		4000	

**Thermal Resistances**

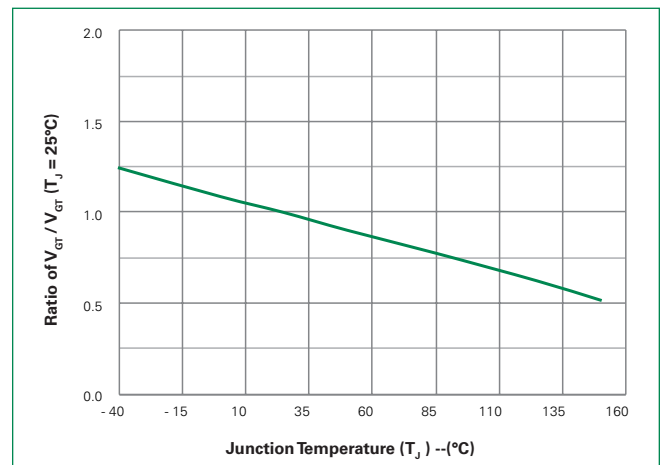
Symbol	Parameter		Value	Unit
R <sub>θ(J-C)</sub>	Junction to case (AC)	SJxx40Ry/SJxx40Ny	0.8	°C/W
R <sub>θ(J-A)</sub>	Junction to ambient	Sxx40Ry	40	°C/W

Note: xx = voltage, y = sensitivity & type

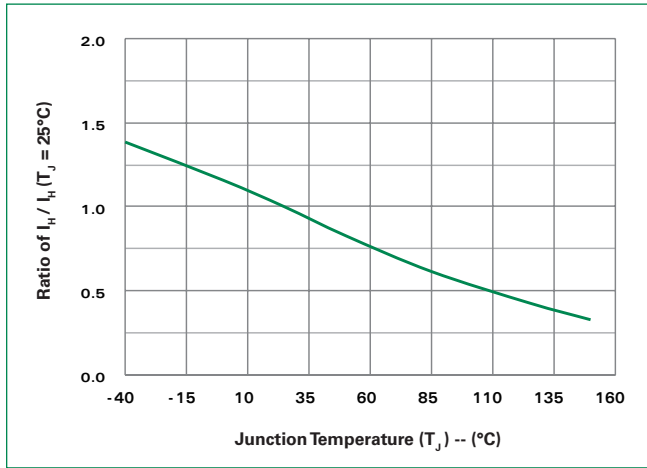
**Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature**



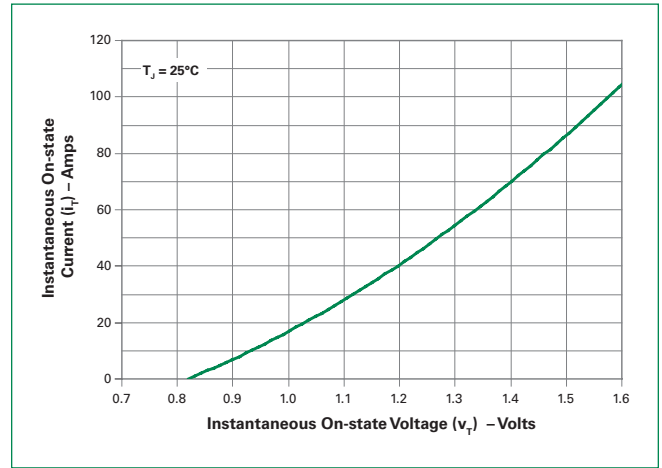
**Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature**



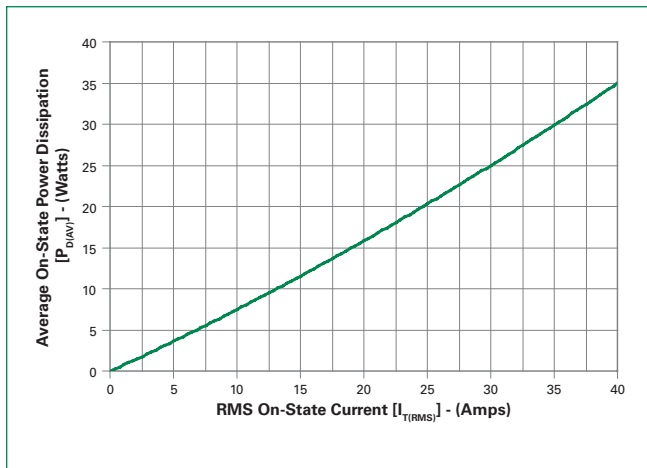
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



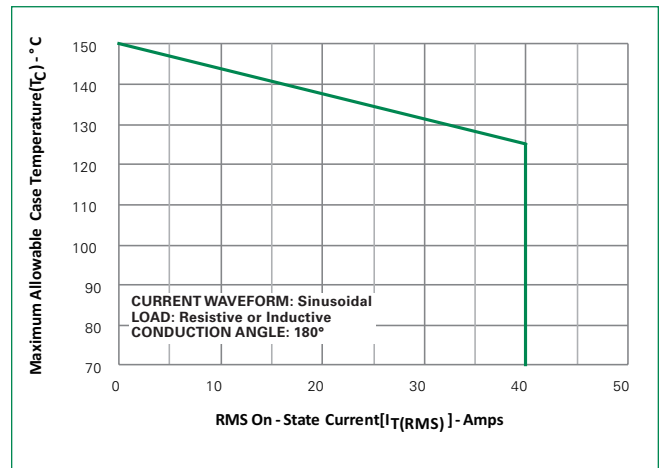
**Figure 4: On-State Current vs. On-State Voltage (Typical)**



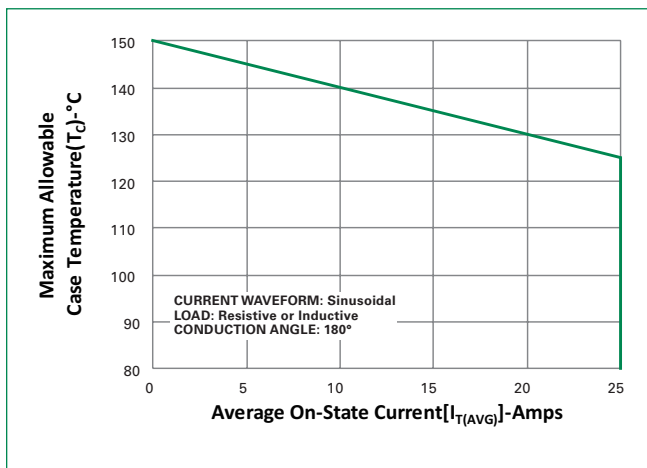
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



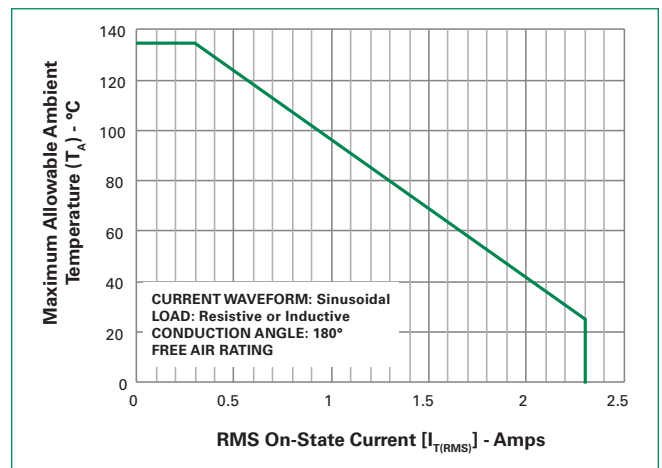
**Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current**



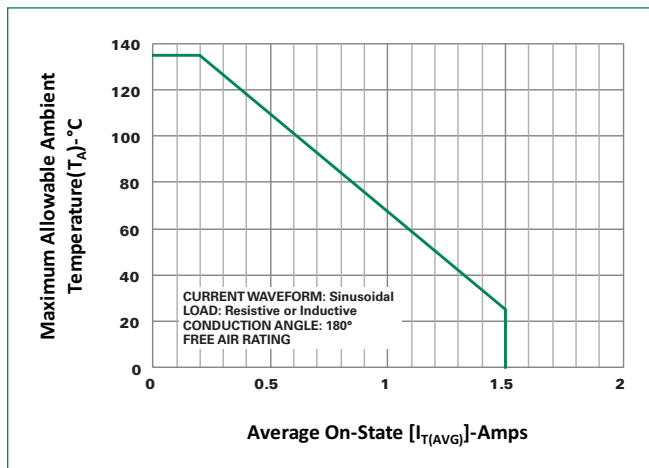
**Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current**



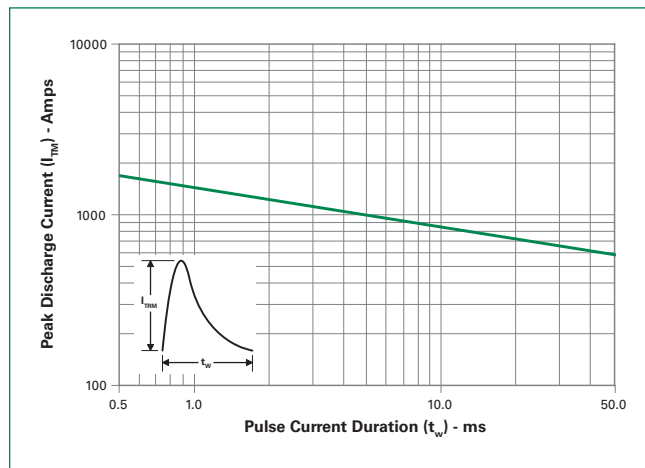
**Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current**



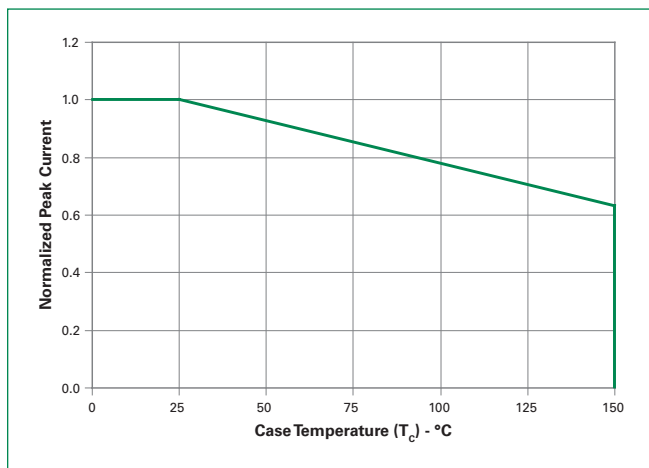
**Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current**



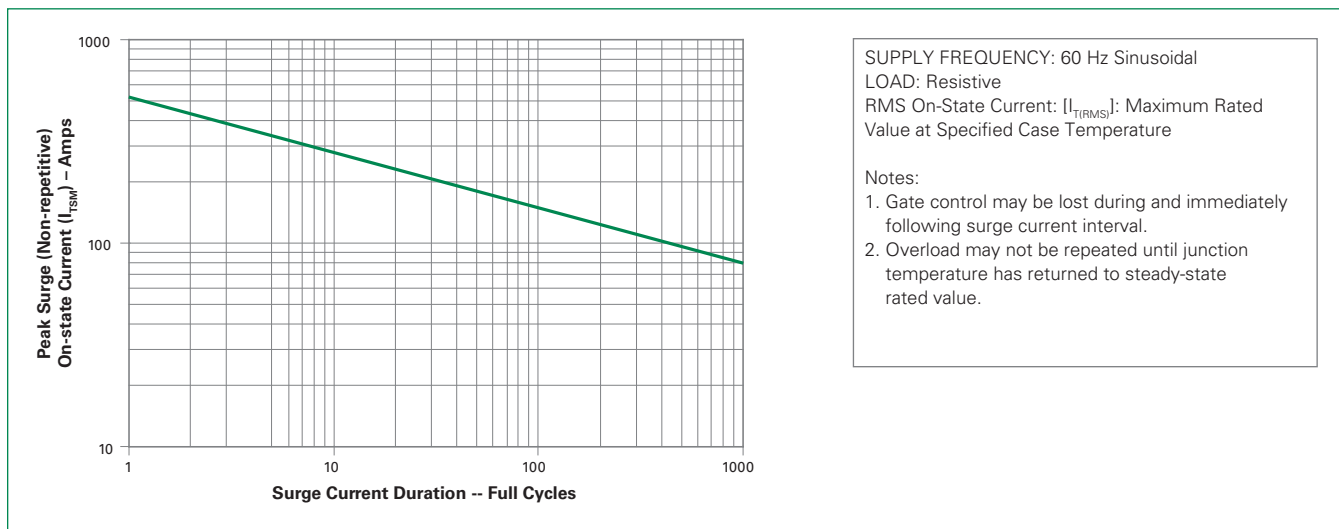
**Figure 10: Peak Capacitor Discharge Current**



**Figure 11: Peak Capacitor Discharge Current Derating**

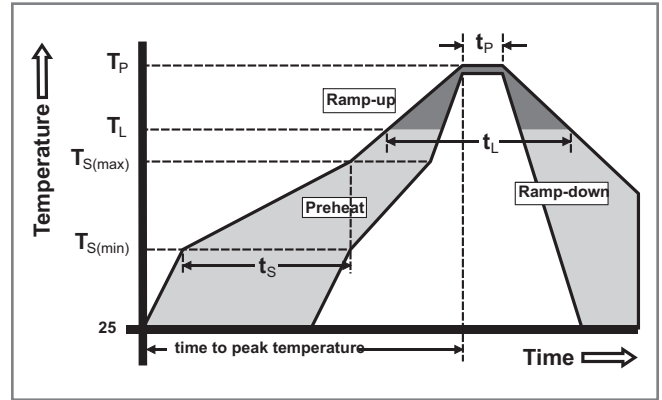


**Figure 12: Surge Peak On-State Current vs. Number of Cycles**



**Soldering Parameters**

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Time ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



**Physical Specifications**

<b>Terminal Finish</b>	100% Matte Tin-plated
<b>Body Material</b>	UL Recognized epoxy meeting flammability rating V-0
<b>Lead Material</b>	Copper Alloy

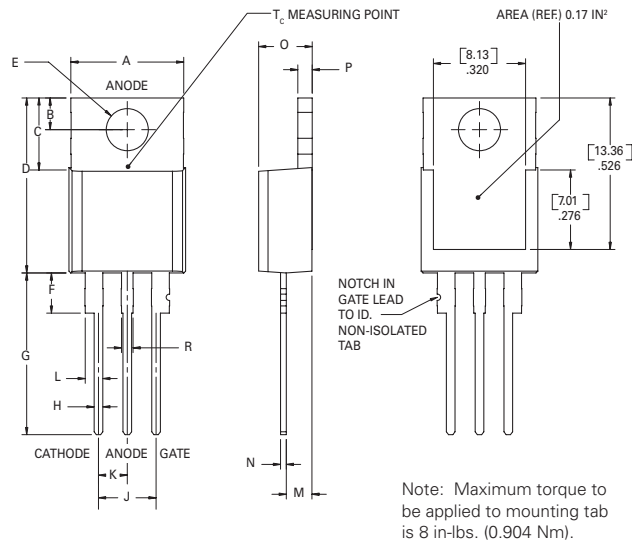
**Design Considerations**

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

**Environmental Specifications**

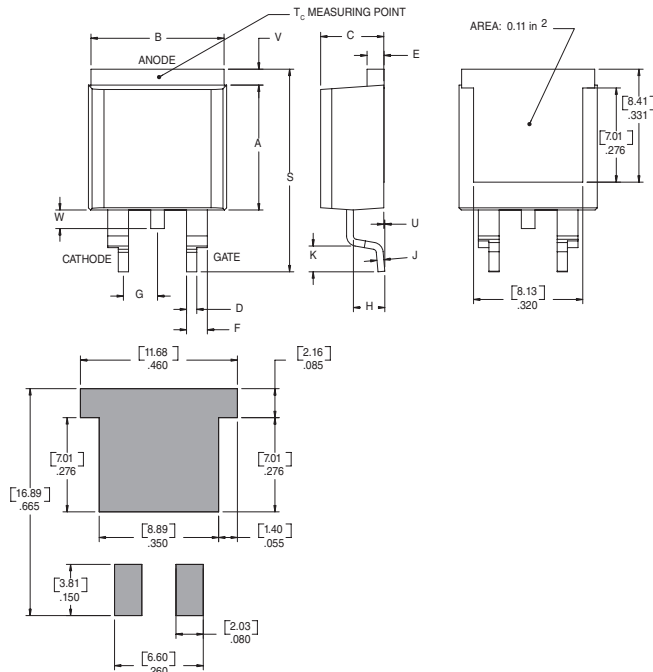
Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 150°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E
<b>Moisture Sensitivity Level</b>	Level 1, JEDEC-J-STD-020D

**Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead**



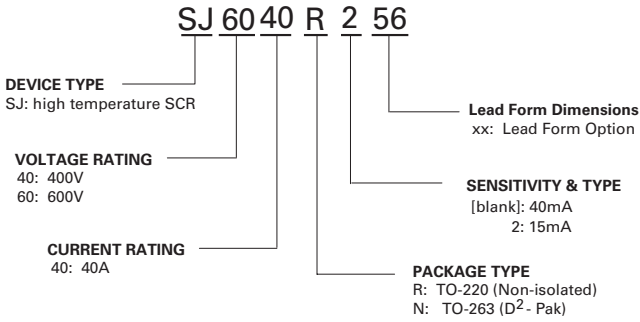
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

**Dimensions — TO-263 (N-package) — D<sup>2</sup>-Pak Surface Mount**

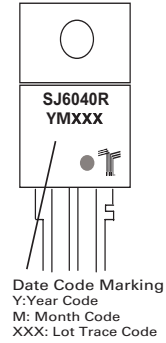


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.63	0.89
E	0.048	0.055	1.22	1.40
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.083	0.093	2.11	2.36
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.87
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

**Part Numbering System**



**Part Marking System**



**Product Selector**

Part Number	Voltage		Gate Sensitivity	Type	Package
	400V	600V			
SJxx40R	X	X	40mA	Standard SCR	TO-220R
SJxx40N	X	X	40mA	Standard SCR	TO-263
SJxx40R2	X	X	15mA	Standard SCR	TO-220R
SJxx40N2	X	X	15mA	Standard SCR	TO-263

Note: xx = Voltage

**Packing Options**

Part Number	Marking	Weight	Packing Mode	Base Quantity
SJxx40RTP	SJxx40R	2.2g	Tube	500 (50 per tube)
SJxx40NTP	SJxx40N	1.6g	Tube	500 (50 per tube)
SJxx40NRP	SJxx40N	1.6g	Embossed Carrier	500
SJxx40R2TP	SJxx40R2	2.2g	Tube	500 (50 per tube)
SJxx40N2RP	SJxx40N2	1.6g	Embossed Carrier	500

Note: xx = Voltage

**Reel Pack (RP) for TO-263 Embossed Carrier Specifications**

**Meets all EIA-481-2 Standards**

